

2SC5363(Tentative)

Silicon NPN epitaxial planer type

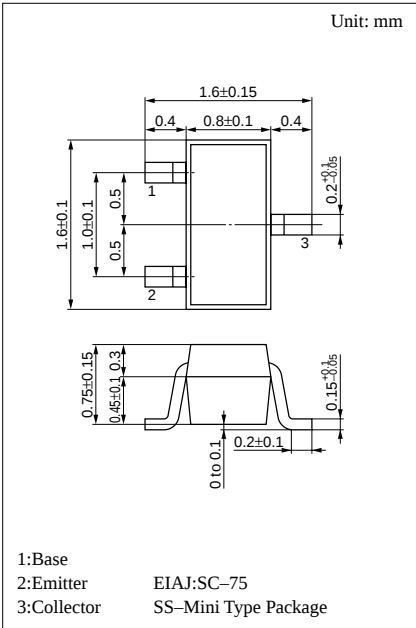
For low-voltage high-frequency amplification

Features

- High transition frequency f_T .
- Small collector output capacitance C_{ob} .
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Absolute Maximum Ratings (Ta=25°C)

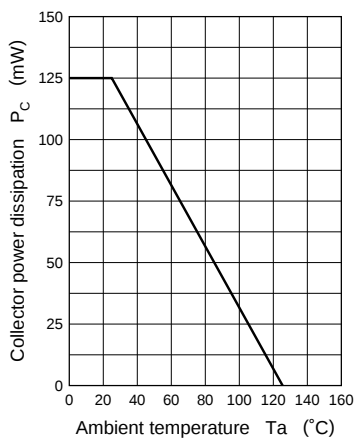
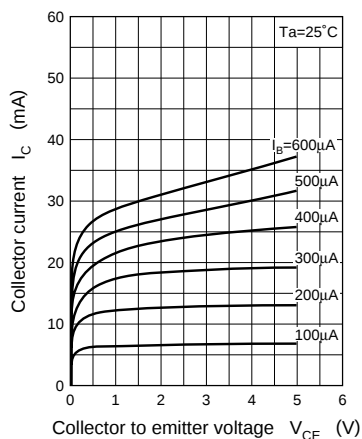
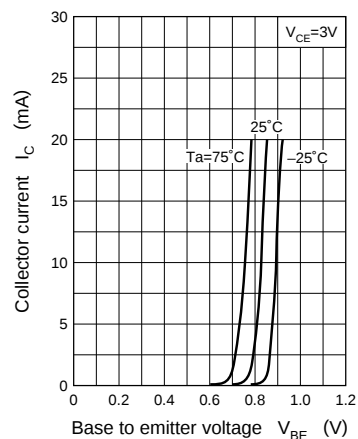
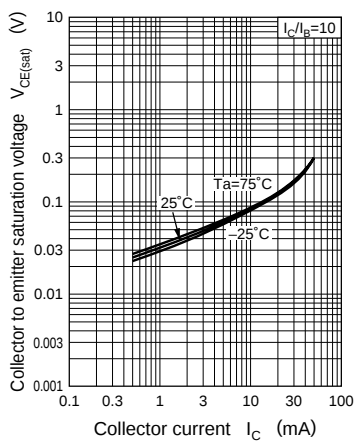
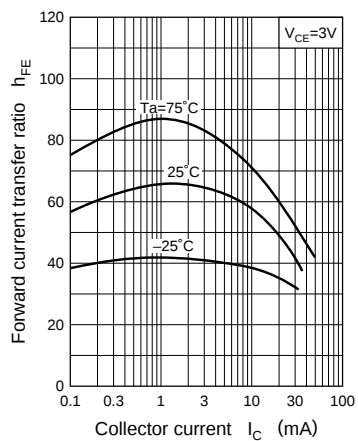
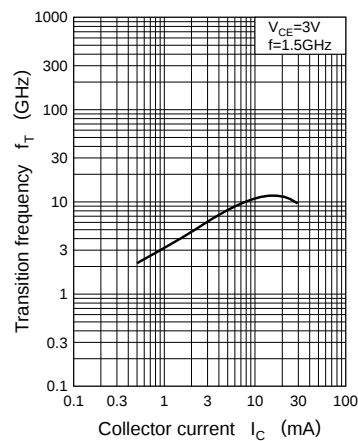
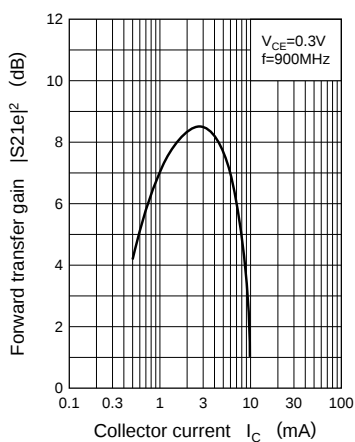
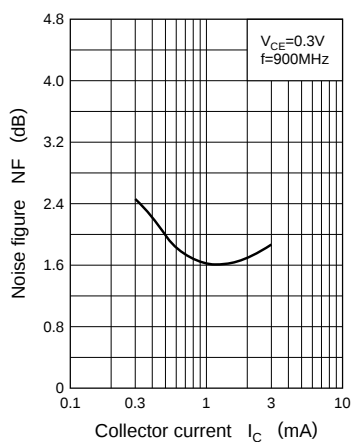
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	9	V
Collector to emitter voltage	V_{CEO}	6	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 ~ +125	°C



Marking symbol : 3Y

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 5V, I_E = 0$			1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 1V, I_C = 0$			1	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 3V, I_C = 10mA$	40	100	200	
Collector output capacitance	C_{ob}	$V_{CB} = 3V, I_E = 0, f = 1MHz$		0.4	0.7	pF
Transition frequency	f_T	$V_{CE} = 3V, I_C = 10mA, f = 1.5GHz$		10		GHz
Foward transfer gain	$ S_{21e} ^2$	$V_{CE} = 0.3V, I_C = 1mA, f = 0.9GHz$		6.5		dB
Noise figure	NF	$V_{CE} = 0.3V, I_C = 1mA, f = 0.9GHz$		1.7		dB

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $|S_{21e}|^2 - I_C$ NF — I_C  $C_{ob} - V_{CB}$ 